2023년 2월 14일(화), 09:00-10:45

Room B (에메랄드 II+III, 5층)

D. Thin Film Process Technology 분과
[TB1-D] Ferroelectrics

좌장: 안지훈 교수(한양대학교), 이웅규 교수(숭실대학교)

TB1-D-1 **09:00-09:15**	**Improvement in Memory Performance of Dual-Switching Memory FET Introducing Gate Charge-Injection and Ferroelectric Layers** Yun-Ju Cho and Sung-Min Yoon *Department of Advanced Materials Engineering for Information and Electronics, Kyung Hee University*
TB1-D-2 **09:15-09:30**	**Dynamics of Domain Wall Motion and Polarization Switching Kinetics of Ferroelectric $Hf_{0.5}Zr_{0.5}O_2$ Thin Film on Different Electrode Materials** Dong Hyun Lee[1,2], Geun Hyeong Park[1,2], Jaewook Lee[1,2], Se Hyun Kim[1,2], and Min Hyuk Park[1,2] *[1]Department of Materials Science and Engineering, Seoul National University, [2]Inter-university Semiconductor Research Center, Seoul National University*
TB1-D-3 **09:30-09:45**	**Study of Ferroelectric TiN/$Hf_{0.5}Zr_{0.5}O_2$/TiN Capacitor Fabricated without Breaking Vacuum** Younghwan Lee[1,2], H. Alex Hsain[2], Shelby S. Fields[3], Samantha T. Jaszewski[3], Jon F. Ihlefeld[3], Gregory N. Parsons[4], and Jacob L. Jones[2] *[1]Department of Materials Science and Engineering, North Carolina State University, [2]Research Institute of Advanced Materials, Seoul National University, [3]Department of Materials Science and Engineering, University of Virginia, [4]Department of Chemical and Biomolecular Engineering, North Carolina State University*
TB1-D-4 **09:45-10:00**	**Investigation of the Ferroelectric Characteristics of $Hf_{1-x}Zr_xO_2$ Films Grown on Mo Electrodes with Various Thicknesses and Compositions** Ju Yong Park[1], Se Hyun Kim[1], Dong Hyun Lee[1], Kun Yang[1], Geun Hyeong Park[1], Younghwan Lee[2], and Min Hyuk Park[1,2] *[1]Department of Materials Science and Engineering, College of Engineering, Seoul National University, [2]Research Institute of Advanced Materials, Seoul National University*
TB1-D-5 **10:00-10:15**	**Ferroelectric Crystallization of Atomic Layer Deposited Ultrathin HfZrO Thin Films through Rapid Cooling Process** Yeon Je Yu[1], Geun Ha Oh[1], Ae Rim Choi[1], Ja-Yong Kim[2], Dohee Kim[2], and Il Kwon Oh[1] *[1]Department of Electrical and Computer Engineering, Ajou University, [2]Revolutionary Technology Center, R&D Division, SK Hynix*
TB1-D-6 **10:15-10:30**	**First Principles-derived Process Optimization to Control the Phase Fractions of Ferroelectric and Antiferroelectric $Hf_{1-x}Zr_xO_2$** Kun Hee Ye[1,2,3], Taeyoung Jeoung[1,2,3], Seungjae Yoon[1,2,3], Cheol Seong Hwang[2,3], and Jung-Hae Choi[1] *[1]Electronic Materials Research Center, KIST, [2]Department of Materials Science and Engineering, Seoul National University, [3]Inter-university Semiconductor Research Center, Seoul National University*
TB1-D-7 **10:30-10:45**	**IGZO Epitaxial Layer를 통한 $Hf_xZr_{1-x}O_2$ 박막의 저온 결정화 유도** 김성호[1], 고운산[2], 이가원[2], 이희덕[2], 조병진[1] *[1]한국과학기술원 전기 및 전자공학부, [2]충남대학교 전자공학과*